

ABSTRACT OF THE DISCLOSURE

A semiconductor integrated circuit device having an internal voltage generating circuit which generates a voltage two or more times higher than an operating voltage while at the same time reducing the voltage applied to a device, thereby ensuring the device reliability. In a charge pump circuit driven by supply voltage VDD, a maximum of $2V_{DD}$ or a similar level voltage is applied between the drain and source of a MOSFET, the MOSFET being connected in series with a conduction MOSFET of the same type, the gate of which is supplied with $V_D - V_{DD}$, or a potential which is VDD lower than V_D , the drain potential before its connection. The gate potential is obtained directly from a node in said charge pump which generates a voltage pulse synchronized with the voltage between the drain and source of that MOSFET, or through another rectifier device branched via a capacitor from the node.